8-Bit Serial or Parallel-Input/ Serial-Output Shift Register

High-Performance Silicon-Gate CMOS



The MC74HC165A is identical in pinout to the LS165. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device is an 8-bit shift register with complementary outputs from the last stage. Data may be loaded into the register either in parallel or in serial form. When the Serial Shift/Parallel Load input is low, the data is loaded asynchronously in parallel. When the Serial Shift/Parallel Load input is high, the data is loaded serially on the rising edge of either Clock or Clock Inhibit (see the Function Table).

The 2-input NOR clock may be used either by combining two independent clock sources or by designating one of the clock inputs to act as a clock inhibit.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 286 FETs or 71.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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MARKING DIAGRAMS



PDIP-16 N SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F





QFN16 MN SUFFIX CASE 485AW



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

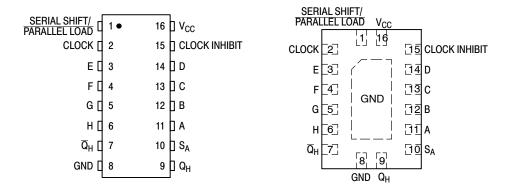


Figure 1. Pin Assignments

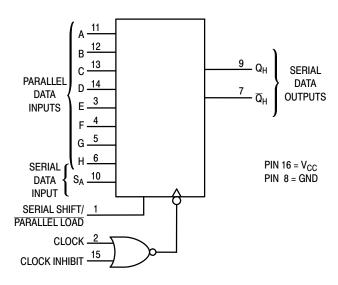


Figure 2. Logic Diagram

FUNCTION TABLE

Inputs			Interna	l Stages	Output			
Serial Shift/ Parallel Load	Clock	Clock Inhibit	SA	A – H	Q_{A}	Q_{B}	Q _H	Operation
L	Х	Х	Х	a h	а	b	h	Asynchronous Parallel Load
H H	\(\sigma \)	L L	L H	X	L H	Q _{An} Q _{An}	Q _{Gn} Q _{Gn}	Serial Shift via Clock
H H	L L	<i>S</i>	L H	X	L H	Q _{An} Q _{An}	Q _{Gn} Q _{Gn}	Serial Shift via Clock Inhibit
H H	X H	H X	X X	X	No Change			Inhibited Clock
Н	L	L	Х	Х		No Change	!	No Clock

X = don't care $Q_{An} - Q_{Gn} = Data shifted from the preceding stage$

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Refere GND)	tt Voltage, Output Voltage (Referenced to			V
T _A	Operating Temperature, All Package Type	es	– 55	+ 125	°C
t _r , t _f	(Figure 1)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 3.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 600 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			v _{cc}	Gua	ranteed Limi	it	
Symbol	Parameter	Test Conditions	V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $ I_{out} \le 20 \mu A$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	0.5 0.9 1.35 1.80	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\label{eq:Vin} \begin{array}{ l l } V_{in} = V_{IH} \text{ or } V_{IL} & I_{out} \leq 2.4 \text{ mA} \\ & I_{out} \leq 4.0 \text{ mA} \\ & I_{out} \leq 5.2 \text{ mA} \end{array}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	V

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			v _{cc}	Guaranteed Limit			
Symbol	Parameter	Test Conditions	V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{split} V_{in} = V_{IH} \text{ or } V_{IL} & \left I_{out} \right \leq 2.4 \text{ mA} \\ \left I_{out} \right \leq 4.0 \text{ mA} \\ \left I_{out} \right \leq 5.2 \text{ mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μА

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (C $_{L}$ = 50 pF, Input t_{r} = t_{f} = 6 ns)

		V _{CC}	Gua	ranteed Limi	t	
Symbol	Parameter	v	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle)	2.0	6	4.8	4	MHz
	(Figures 1 and 8)	3.0	18	17	15	
		4.5	30	24	20	
		6.0	35	28	24	
t _{PLH} ,	Maximum Propagation Delay, Clock (or Clock Inhibit) to Q_H or \overline{Q}_H	2.0	150	190	225	ns
t _{PHL}	(Figures 1 and 8)	3.0	52	63	65	
		4.5	30	38	45	
		6.0	26	33	38	
t _{PLH} ,	Maximum Propagation Delay, Serial Shift/ $\overline{Parallel}$ Load to Q_H or \overline{Q}_H	2.0	175	220	265	ns
t _{PHL}	(Figures 2 and 8)	3.0	58	70	72	
		4.5	35	44	53	
		6.0	30	37	45	
t _{PLH} ,	Maximum Propagation Delay, Input H to Q_H or \overline{Q}_H	2.0	150	190	225	ns
t _{PHL}	(Figures 3 and 8)	3.0	52	63	65	
		4.5	30	38	45	
		6.0	26	33	38	
t _{TLH} ,	Maximum Output Transition Time, Any Output	2.0	75	95	110	ns
t _{THL}	(Figures 1 and 8)	3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
C _{in}	Maximum Input Capacitance	_	10	10	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Package)*	40	pF

^{*}Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

TIMING REQUIREMENTS (Input $t_r = t_f = 6 \text{ ns}$)

			Guar	anteed Lim	it	
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{su}	Minimum Setup Time, Parallel Data Inputs to Serial Shift/Parallel Load	2.0	75	95	110	ns
Su	(Figure 4)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t _{su}	Minimum Setup Time, Input SA to Clock (or Clock Inhibit)	2.0	75	95	110	ns
	(Figure 5)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t _{su}	Minimum Setup Time, Serial Shift/Parallel Load to Clock (or Clock Inhibit)	2.0	75	95	110	ns
	(Figure 6)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t _{su}	Minimum Setup Time, Clock to Clock Inhibit	2.0	75	95	110	ns
	(Figure 7)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t _h	Minimum Hold Time, Serial Shift/Parallel Load to Parallel Data Inputs	2.0	5	5	5	ns
	(Figure 4)	3.0	5	5	5	
		4.5	5	5	5	
		6.0	5	5	5	
t _h	Minimum Hold Time, Clock (or Clock Inhibit) to Input SA	2.0	5	5	5	ns
	(Figure 5)	3.0	5	5	5	
		4.5	5	5	5	
		6.0	5	5	5	
t _h	Minimum Hold Time, Clock (or Clock Inhibit) to Serial Shift/Parallel Load	2.0	5	5	5	ns
	(Figure 6)	3.0	5	5	5	
		4.5	5	5	5	
		6.0	5	5	5	
t_{rec}	Minimum Recovery Time, Clock to Clock Inhibit	2.0	75	95	110	ns
	(Figure 7)	3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t _w	Minimum Pulse Width, Clock (or Clock Inhibit)	2.0	70	90	100	ns
	(Figure 1)	3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
t _w	Minimum Pulse width, Serial Shift/Parallel Load	2.0	70	90	100	ns
	(Figure 2)	3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
t_r , t_f	Maximum Input Rise and Fall Times	2.0	1000	1000	1000	ns
	(Figure 1)	3.0	800	800	800	
		4.5	500	500	500	
		6.0	400	400	400	

PIN DESCRIPTIONS

INPUTS

A, B, C, D, E, F, G, H (Pins 11, 12, 13, 14, 3, 4, 5, 6)

Parallel Data inputs. Data on these inputs are asynchronously entered in parallel into the internal flip-flops when the Serial Shift/Parallel Load input is low.

SA (Pin 10)

Serial Data input. When the Serial Shift/Parallel Load input is high, data on this pin is serially entered into the first stage of the shift register with the rising edge of the Clock.

CONTROL INPUTS

Serial Shift/Parallel Load (Pin 1)

Data-entry control input. When a high level is applied to this pin, data at the Serial Data input (SA) are shifted into the register with the rising edge of the Clock. When a low level is applied to this pin, data at the Parallel Data inputs are asynchronously loaded into each of the eight internal stages.

Clock, Clock Inhibit (Pins 2, 15)

Clock inputs. These two clock inputs function identically. Either may be used as an active-high clock inhibit. However, to avoid double clocking, the inhibit input should go high only while the clock input is high.

The shift register is completely static, allowing Clock rates down to DC in a continuous or intermittent mode.

OUTPUTS

Q_H, Q_H (Pins 9, 7)

Complementary Shift Register outputs. These pins are the noninverted and inverted outputs of the eighth stage of the shift register.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC165ANG	PDIP-16 (Pb-Free)	500 Units / Rail
MC74HC165ADG		48 Units / Rail
MC74HC165ADR2G	SOIC-16 (Pb-Free)	2500 Units / Reel
NLV74HC165ADR2G*	(, 2, 1, 33)	2500 Units / Reel
MC74HC165ADTR2G	TSSOP-16	2500 Units / Reel
NLV74HC165ADTR2G*	(Pb-Free)	2500 Units / Reel
MC74HC165AMNTWG	QFN16	3000 Units / Reel
MC74HC165AMN2TWG	74HC165AMN2TWG (Pb-Free)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

SWITCHING WAVEFORMS

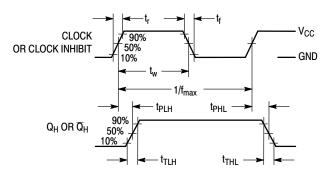


Figure 3. Serial-Shirt Mode

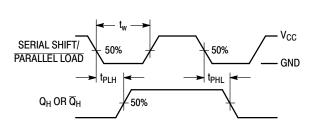


Figure 4. Parallel-Load Mode

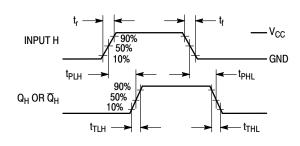


Figure 5. Parallel-Load Mode

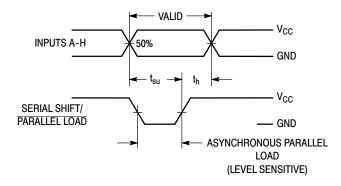


Figure 6. Parallel-Load Mode

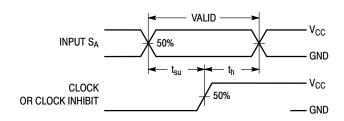


Figure 7. Serial-Shift Mode

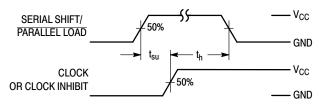


Figure 8. Serial-Shift Mode

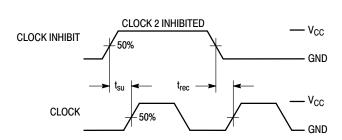
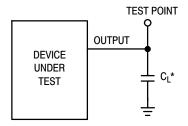


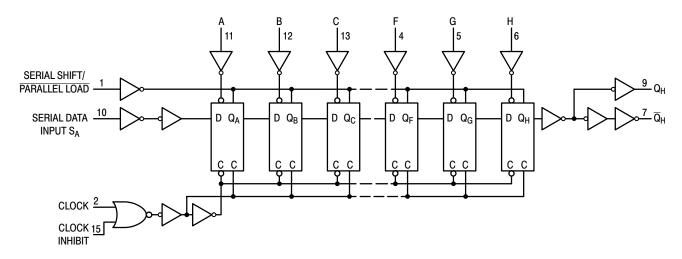
Figure 9. Serial-Shift, Clock-Inhibit Mode



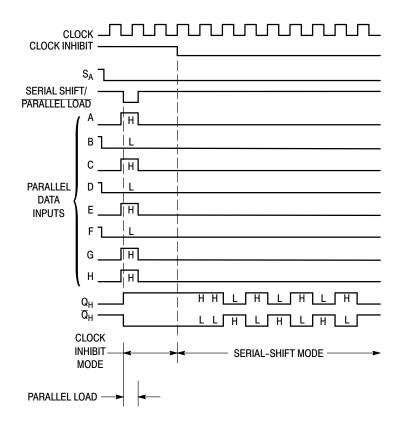
*Includes all probe and jig capacitance

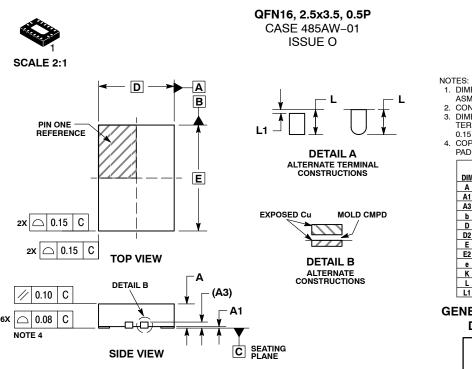
Figure 10. Test Circuit

EXPANDED LOGIC DIAGRAM



TIMING DIAGRAM





0.15 C A B

E2

⊕ 0.15 C A B

16X b

Ф

0.10

0.05 С NOTE 3

CAB

D2

BOTTOM VIEW

DETAIL A

е e/2 **DATE 11 DEC 2008**

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLEHANGING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. DIMENSIONS 6 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN
- 1.15 AND 0.30 MM FROM TERMINAL.
 COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.80	1.00		
A1	0.00	0.05		
A3	0.20	REF		
b	0.20	0.30		
D	2.50	BSC		
D2	0.85	1.15		
Е	3.50	BSC		
E2	1.85	2.15		
е	0.50	BSC		
K	0.20			
L	0.35	0.45		
L1		0.15		

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code

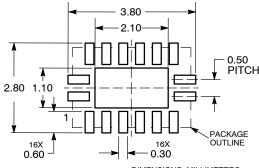
Α = Assembly Location = Wafer Lot L

V - Year = Work Week W = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

SOLDERING FOOTPRINT*

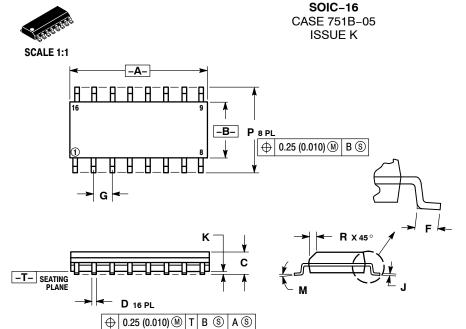


DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	DCUMENT NUMBER: 98AON36347E Electronic versions are uncontrolled except when accessed directly from the Printed versions are uncontrolled except when stamped "CONTROLLED CO		
DESCRIPTION:	QFN16, 2.5X3.5, 0.5P		PAGE 1 OF 1

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DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.		PIN 1.		PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	E #1	
2.			ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.		7.	EMITTER, #2	7.	COLLECTOR, #4		
8.	COLLECTOR			8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE		CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.		11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER		CATHODE	12.		12.			
13.	BASE		CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	SOI DEDING	FOOTPRINT
14.	COLLECTOR		NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDENING	FOOTFRINT
15.	EMITTER		ANODE	15.	EMITTER, #4	15.	BASE, #1	:	8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	6	.40 —
								-	0
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12 ← ➤
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				,
2.	DRAIN. #1		CATHODE	2.	COMMON DRAIN (OUTPUT	1		. 🗀 1	16
3.	DRAIN, #2		CATHODE	3.	COMMON DRAIN (OUTPUT			↓ — ·	· · ·
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	,		<u>-</u>	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT	1	16	6X 🛣	
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPUT			58 ^J 🖂	' <u> </u>
7.	DRAIN, #4	7.		7.	COMMON DRAIN (OUTPUT		0.	56	ı
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH `	,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT)			
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT	ń			
13.	GATE, #2	13.	ANODE	13.	GATE N-CH	,			
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT)			PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT				<u> </u>
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH				
	*							□ 8	9 + - + -
								<u> </u>	ı
									DIMENSIONS MILLIMETERS
									DIMENSIONS: MILLIMETERS

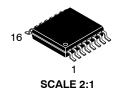
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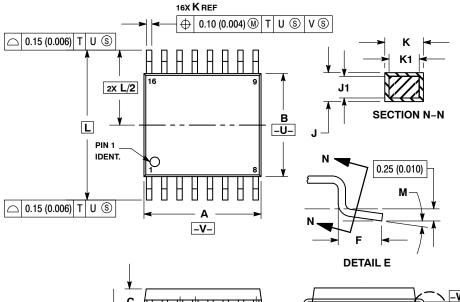
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



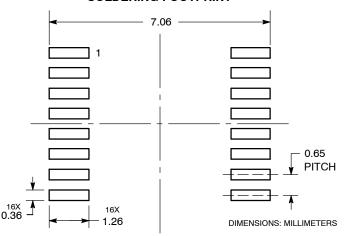
NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026 BSC		
H	0.18	0.28	0.007	0.011	
7	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
М	0 °	8 °	0 °	8 °	

SOLDERING FOOTPRINT

G



GENERIC MARKING DIAGRAM*

168888888 XXXX XXXX **ALYW** 188888888

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	TSSOP-16		PAGE 1 OF 1		

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